

Silicon NPN Power Transistors

2SC1922

DESCRIPTION

- With TO-3 package
- High breakdown voltage
- High speed switching

APPLICATIONS

- For TV horizontal output applications

PINNING (See Fig.2)

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Emitter |
| 3 | Collector |

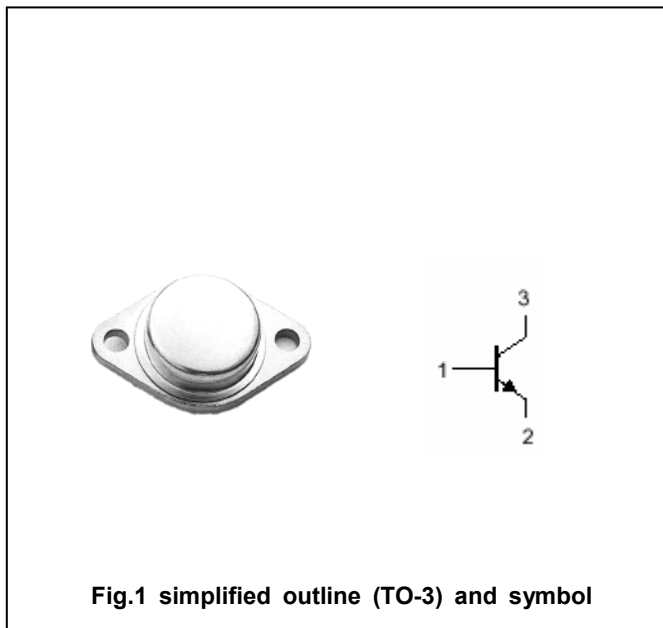


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|---------------------------|----------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | 1500 | V |
| V _{CEO} | Collector-emitter voltage | Open base | 800 | V |
| V _{EBO} | Emitter-base voltage | Open collector | 6 | V |
| I _C | Collector current | | 2.5 | A |
| P _T | Total power dissipation | T _C =25°C | 50 | W |
| T _j | Junction temperature | | 150 | °C |
| T _{stg} | Storage temperature | | -65~150 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | VALUE | UNIT |
|---------------------|--|-------|------|
| R _{th j-c} | Thermal resistance from junction to case | 2.5 | °C/W |

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{CEO(SUS)} | Collector-emitter sustaining voltage | I _C =0.1A ; I _B =0 | 800 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =1mA ; I _C =0 | 6 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =2A; I _B =0.6A | | | 5.0 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =2A; I _B =0.6A | | | 1.5 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =600V; I _E =0 | | | 10 | μA |
| I _{EBO} | Emitter cut-off current | V _{EB} =5V; I _C =0 | | | 10 | μA |
| h _{FE} | DC current gain | I _C =0.5A ; V _{CE} =5V | 8 | | 40 | |

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PACKAGE OUTLINE

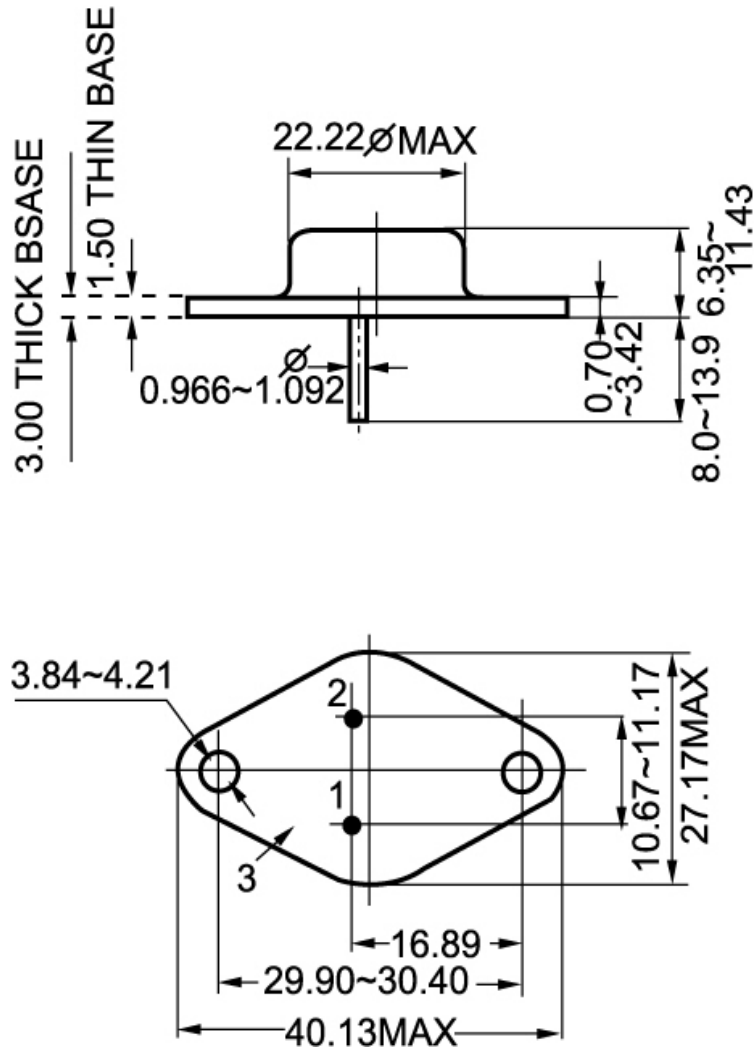


Fig.2 Outline dimensions